Unit in mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

HN4K03JU

High Speed Switching Applications Analog Switch Applications

- High input impedance
- Low gate threshold voltage: $V_{th} = 0.5 \sim 1.5 V$
- Excellent switching times
- Small package

Maximum Ratings (Ta = 25°C) (Q1, Q2 Common)

Characteristic	Symbol	Rating	Unit
Drain-Source voltage	V _{DS}	20	V
Gate-Source voltage	V _{GSS}	10	V
DC Drain current	۱ _D	100	mA
Drain power dissipation	P _D *	200	mW
Channel temperature	T _{ch}	150	°C
Storage temperature range	T _{stg}	-55~150	°C
* : Total rating			



Weight: 6.2mg

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Characteristic		Symbol	Test Condition	Min.	Тур.	Max.	Unit
Gate leakage curre	ent	I _{GSS}	V _{GS} = 10V, V _{DS} = 0	—	_	1	μA
Drain-Source brea	kdown voltage	V (BR) DSS	$I_{\rm D}$ = 100µA, V _{GS} = 0	20	_	_	V
Drain cut-off curren	nt	I _{DSS}	$V_{DS} = 20V, V_{GS} = 0$	_	_	1	μA
Gate threshold vol	tage	V _{th}	V _{DS} = 3V, I _D = 0.1mA	0.5	_	1.5	V
Forward transfer a	dmittance	Y _{fs}	V _{DS} = 3V, I _D = 10mA	25	50	—	mS
Drain-Source ON r	resistance	R _{DS (ON)}	I _D = 10mA, V _{GS} = 2.5V	_	8	12	Ω
Input capacitance		C _{iss}	$V_{DS} = 3V, V_{GS} = 0, f = 1MH_z$	_	8.5	_	pF
Reverse transfer c	apacitance	C _{rss}	$V_{DS} = 3V, V_{GS} = 0, f = 1MH_z$	_	3.3	_	pF
Output capacitance	e	C _{oss}	$V_{DS} = 3V, V_{GS} = 0, f = 1MH_z$	_	9.3	_	pF
Switching time	Turn-on time	t _{on}	V _{DD} = 3V, I _D = 10mA V _{GS} = 0~2.5V	_	0.16	_	
	Turn-off time	t _{off}	V _{DD} = 3V, I _D = 10mA V _{GS} = 0~2.5V	_	0.15	_	μs

Equivalent Circuit (Top View)

Marking





(Q1, Q2 Common) Switching Time Test Circuit



(Q1, Q2 Common)

